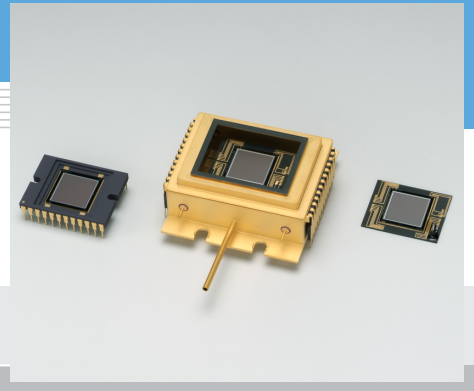


CCD area image sensor S9736 series



512 × 512 pixels, front-illuminated FFT-CCDs

S9736 series is a family of FFT-CCD area image sensors specifically designed for low-light-level detection in scientific applications. S9736 series also features low noise and low dark current (MPP mode operation). These enable low-light-level detection and long integration time, thus achieving a wide dynamic range.

Three different packages (ceramic DIP, metal, plate type) are provided. Metal package type (S9736-02) has a four-stage TE-cooled element built into the same package for thermoelectric cooling. At room temperature operation, the device can be cooled down to -70 °C with using forced air cooling. In addition, since both the CCD chip and TE-cooled element are hermetically sealed, no dry air is required, thus allowing easy handling.

Features

- 512 (H) × 512 (V) pixel format
- Pixel size: 24 × 24 μm
- 100 % fill factor
- Wide dynamic range
- Low dark current
- Low readout noise
- MPP operation
- 3 types of packages are available

Applications

- Astronomy
- Scientific measuring instrument
- Fluorescence spectrometer
- Raman spectrophotometer
- Optical and spectrophotometric analyzer
- For low-light-level detection requiring

General ratings

Parameter	S9736-01	S9736-02	S9736-03
CCD structure	Full frame transfer		
Fill factor	100 %		
Number of active pixels	512 (H) × 512 (V)		
Pixel size	24 (H) × 24 (V) μm		
Active area	12.288 (H) × 12.288 (V) mm		
Vertical clock phase	2 phase		
Horizontal clock phase	2 phase		
Output circuit	One-stage MOSFET source follower		
Cooling	Non-cooled	Four-stage TE-cooled	Non-cooled
Package	24-pin ceramic DIP	28-pin metal package	Plate type
Window	None	AR coated Sapphire	None

■ Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Operating temperature	Topr	-50	-	+30	°C
Storage temperature	Tstg	-50	-	+70	°C
CCD cooling temperature	-	-70	-	+30	°C
OD voltage	VOD	-0.5	-	+25	V
RD voltage	VRD	-0.5	-	+18	V
ISV voltage	VISV	-0.5	-	+18	V
ISH voltage	VISH	-0.5	-	+18	V
IGV voltage	VIG1V, VIG2V	-15	-	+15	V
IGH voltage	VIG1H, VIG2H	-15	-	+15	V
SG voltage	VSG	-15	-	+15	V
OG voltage	VOG	-15	-	+15	V
RG voltage	VRG	-15	-	+15	V
TG voltage	VTG	-15	-	+15	V
Vertical clock voltage	VP1V, VP2V	-15	-	+15	V
Horizontal clock voltage	VP1H, VP2H	-15	-	+15	V

■ Operating conditions (MPP mode, Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Output transistor drain voltage	VOD	18	20	22	V	
Reset drain voltage	VRD	12	13	14	V	
Output gate voltage	VOG	-0.5	2	-	V	
Substrate voltage	VSS	-	0	-	V	
Test point (vertical input source)	VISV	-	VRD	-	V	
Test point (horizontal input source)	VISH	-	VRD	-	V	
Test point (vertical input gate)	VIG1V, VIG2V	-8	0	-	V	
Test point (horizontal input gate)	VIG1H, VIG2H	-8	0	-	V	
Vertical shift register clock voltage	High	VP1VH, VP2VH	0	3	6	V
	Low	VP1VL, VP2VL	-9	-8	-7	
Horizontal shift register clock voltage	High	VP1HH, VP2HH	0	3	6	V
	Low	VP1HL, VP2HL	-9	-8	-7	
Summing gate voltage	High	VSGH	0	3	6	V
	Low	VSGL	-9	-8	-7	
Reset gate voltage	High	VRGH	0	3	6	V
	Low	VRGL	-9	-8	-7	
Transfer gate voltage	High	VTGH	0	3	6	V
	Low	VTGL	-9	-8	-7	

■ Electrical characteristics (Ta=25 °C)

Parameter	Symbol	Remark	Min.	Typ.	Max.	Unit
Signal output frequency	fc	-	-	0.1	1	MHz
Vertical shift register capacitance	CP1V, CP2V	-	-	6000	-	pF
Horizontal shift register capacitance	CP1H, CP2H	-	-	200	-	pF
Summing gate capacitance	CSG	-	-	5	-	pF
Reset gate capacitance	CRG	-	-	5	-	pF
Transfer gate capacitance	CTG	-	-	50	-	pF
Transfer efficiency	CTE	*1	0.99995	0.99999	-	-
DC output level	Vout	*2	12	15	18	V
Output impedance	Zo	*2	-	3	-	kΩ
Power dissipation	P	*2, *3	-	15	-	mW

*1: Charge transfer efficiency per pixel, measured at half of the full well capacity.

*2: The values depend on the load resistance. (VOD=20 V, Load resistance=22 kΩ)

*3: Power dissipation of the on-chip amplifier.

■ Pin connections (S9736-02)

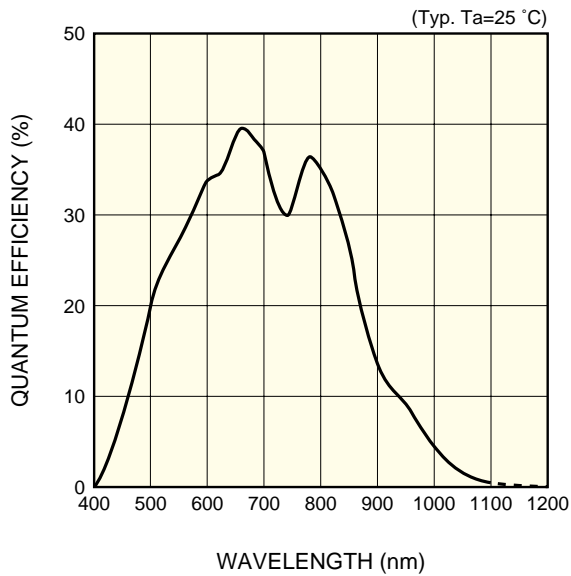
Pin No.	Symbol	Description	Remark
1	P-	TE-cooler-	
2	NC		
3	SS	Substrate (GND)	
4	NC		
5	ISV	Test point (vertical input source)	Shorted to RD
6	IG2V	Test point (vertical input gate-2)	Shorted to 0 V
7	IG1V	Test point (vertical input gate-1)	Shorted to 0 V
8	RG	Reset gate	
9	RD	Reset drain	
10	OS	Output transistor source	
11	OD	Output transistor drain	
12	OG	Output gate	
13	SG	Summing gate	Same timing as P2H
14	P+	TE-cooler+	
15	TSH1	Temperature sensor (hot side)	
16	TSC1	Temperature sensor (cool side)	
17	TSC2	Temperature sensor (cool side)	
18	P2H	CCD horizontal register clock-2	
19	P1H	CCD horizontal register clock-1	
20	IG2H	Test point (horizontal input gate-2)	Shorted to 0 V
21	IG1H	Test point (horizontal input gate-1)	Shorted to 0 V
22	ISH	Test point (horizontal input source)	Shorted to RD
23	P2V	CCD vertical register clock-2	
24	P1V	CCD vertical register clock-1	
25	TG	Transfer gate	Same timing as P2V *12
26	NC		
27	NC		
28	TSH2	Temperature sensor (hot side)	

■ Pad connections (S9736-03)

Pad No.	Symbol	Description	Remark
1	RG	Reset gate	
2	RD	Reset drain	
3	OS	Output transistor source	
4	OD	Output transistor drain	
5	OG	Output gate	
6	SG	Summing gate	
7	NC		
8	NC		
9	P2H	CCD horizontal register clock-2	
10	P1H	CCD horizontal register clock-1	
11	IG2H	Test point (horizontal input gate-2)	
12	IG1H	Test point (horizontal input gate-1)	
13	ISH	Test point (horizontal input source)	
14	P2V	CCD vertical register clock-2	
15	P1V	CCD vertical register clock-1	
16	TG	Transfer gate	Same timing as P2V*12
17	NC		
18	NC		
19	NC		
20	SS	Substrate (GND)	
21	NC		
22	ISV	Test point (vertical input source)	
23	IG2V	Test point (vertical input gate-2)	
24	IG1V	Test point (vertical input gate-1)	

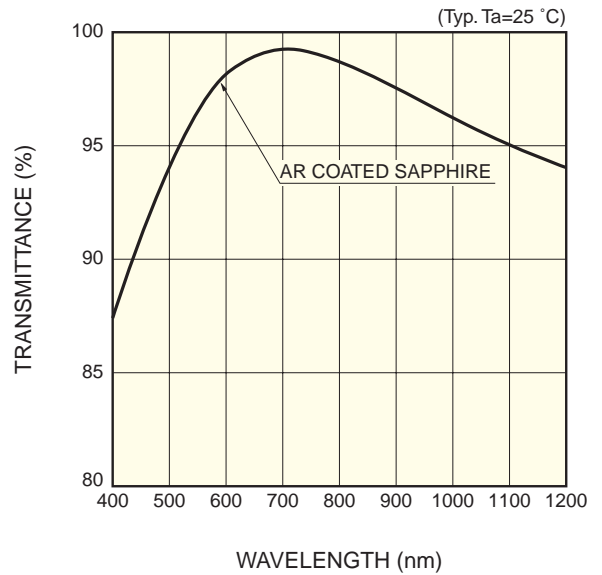
*12: TG is an isolation gate between vertical register and horizontal register.
In standard operation, the same pulse of P2V should be applied to the TG.

■ Spectral response (without window)



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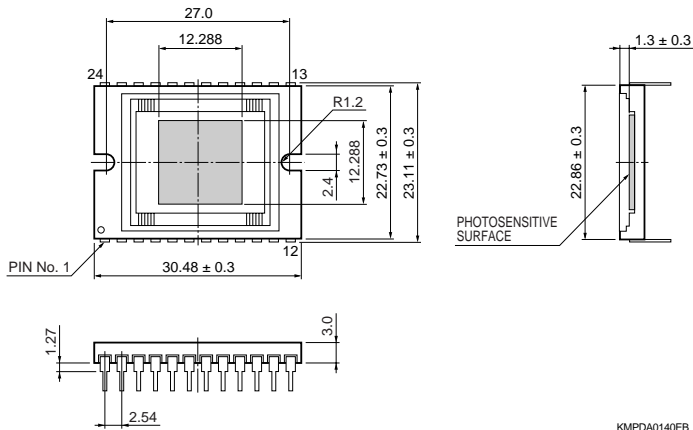
■ Spectral transmittance characteristics of window material



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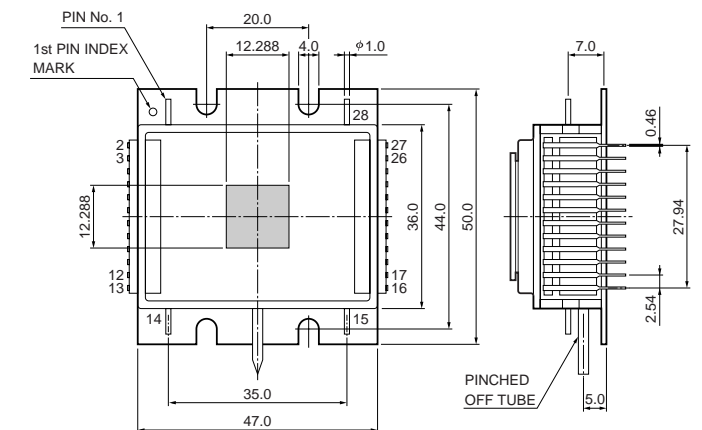
■ Dimensional outlines (unit: mm)

S9736-01



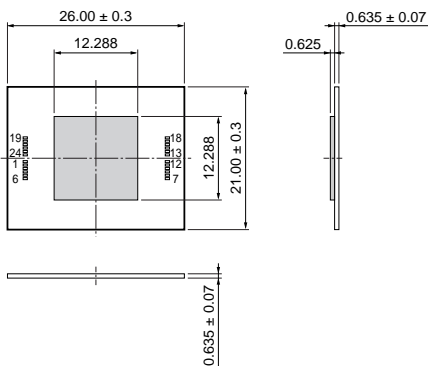
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S9736-02



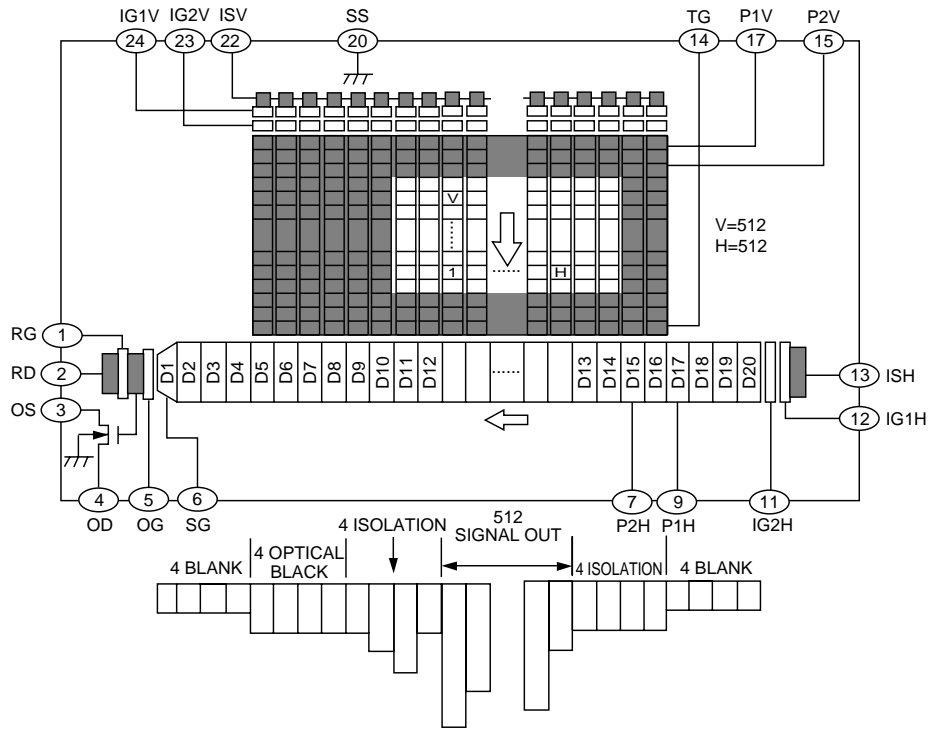
KMPDA0142EB

S9736-03



KMPDA0183EA

■ Device structure, line output format (S9736-01)



KMPDC0207EA

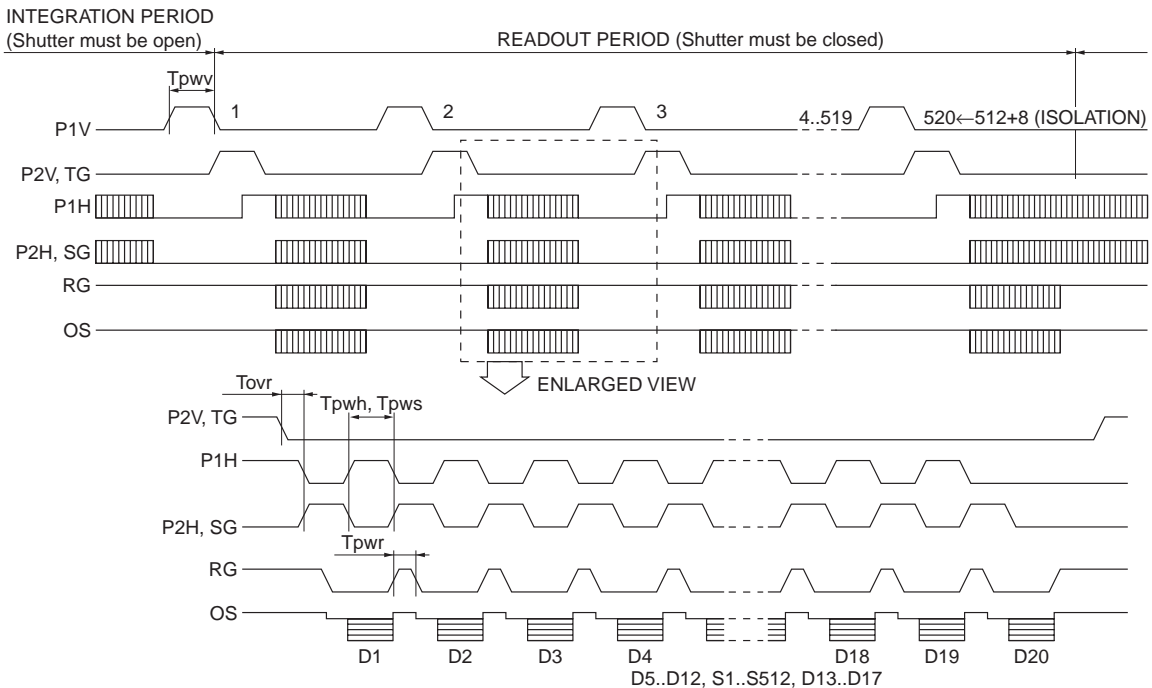
Pixel format

Left ← Horizontal Direction → Right						
Blank	Optical Black	Isolation	Effective	Isolation	Optical Black	Blank
4	4	4	512	4	-	4

Top ← Vertical Direction → Bottom		
Isolation	Effective	Isolation
4	512	4

■ Timing chart

● Area scanning 1 (low dark current mode)

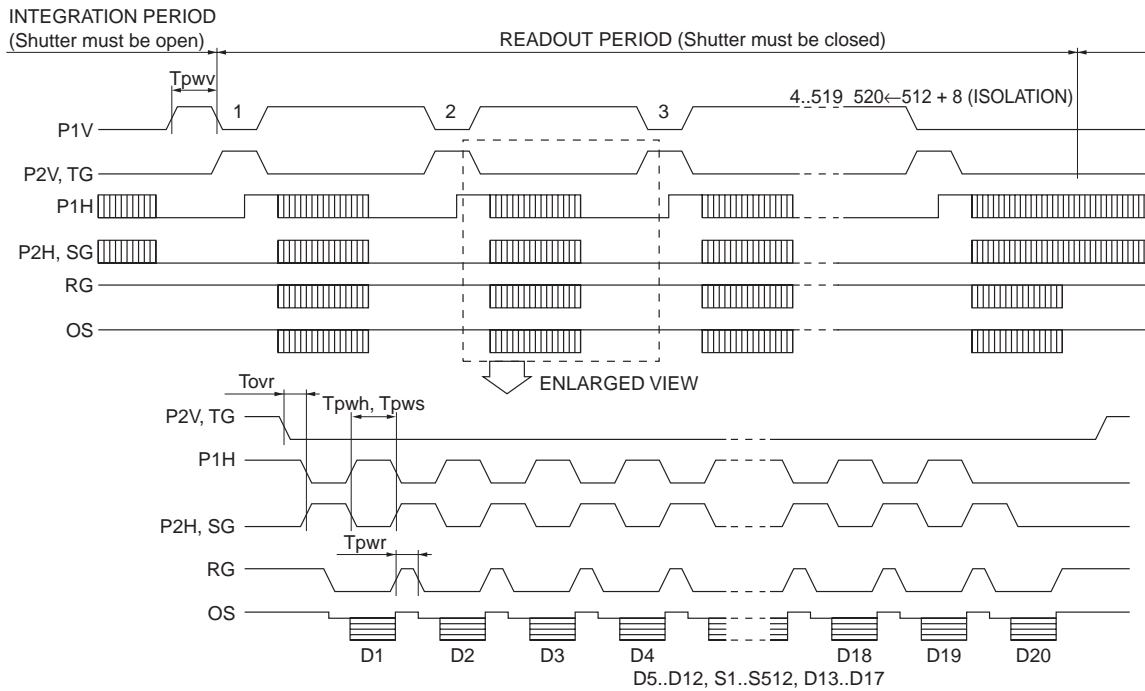


KMPDC0208EA

Parameter		Symbol	Remark	Min.	Typ.	Max.	Unit
P1V	Pulse width	Tp _{pwv}	*13	6	18	-	μs
P2V, TG	Rise and fall time	Tp _{rv} , Tp _{fv}		200	-	-	ns
P1H, P2H	Pulse width	Tp _{wh}	*13	500	5000	-	ns
	Rise and fall time	Tp _{rh} , Tp _{fh}		10	-	-	ns
	Duty ratio	-		-	50	-	%
SG	Pulse width	Tp _{ws}	-	500	5000	-	ns
	Rise and fall time	Tp _{rs} , Tp _{fs}		10	-	-	ns
	Duty ratio	-		-	50	-	%
RG	Pulse width	Tp _{wr}	-	100	500	-	ns
	Rise and fall time	Tp _{rr} , Tp _{fr}		5	-	-	ns
TG – P1H	Overlap time	To _{vr}	-	3	6	-	μs

*13: Symmetrical pulses should be overlapped at 50 % of maximum amplitude.

● Area scanning 2 (large full well mode)



KMPDC0209EA

Parameter		Symbol	Remark	Min.	Typ.	Max.	Unit
P1V	Pulse width	Tp _{pwv}	*14	6	18	-	μs
P2V, TG	Rise and fall time	Tp _{rv} , Tp _{fv}		200	-	-	ns
P1H, P2H	Pulse width	Tp _{wh}	*14	500	5000	-	ns
	Rise and fall time	Tp _{rh} , Tp _{fh}		10	-	-	ns
	Duty ratio	-		-	50	-	%
SG	Pulse width	Tp _{ws}	-	500	5000	-	ns
	Rise and fall time	Tp _{rs} , Tp _{fs}		10	-	-	ns
	Duty ratio	-		-	50	-	%
RG	Pulse width	Tp _{wr}	-	100	500	-	ns
	Rise and fall time	Tp _{rr} , Tp _{fr}		5	-	-	ns
TG – P1H	Overlap time	To _{vr}	-	3	6	-	μs

*14: Symmetrical pulses should be overlapped at 50 % of maximum amplitude.

■ Specifications of built-in TE-cooler (S9736-02)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal resistance	Rint	Ta=27 °C	-	1.6	-	Ω
Maximum current *15	I _{max}	Th *16=27 °C ΔT *17=ΔT _{max}	-	-	4.4	A
Maximum voltage	V _{max}	Th *16=27 °C ΔT=ΔT _{max} I=I _{max}	-	-	7.4	V
Maximum heat absorption *18	Q _{max}	Tc *19=Th *16=27 °C I=I _{max}	-	-	3.0	W
Maximum temperature at hot side	-		-	-	50	°C
CCD temperature	-	Ta=25 °C	-	-70	-50	°C

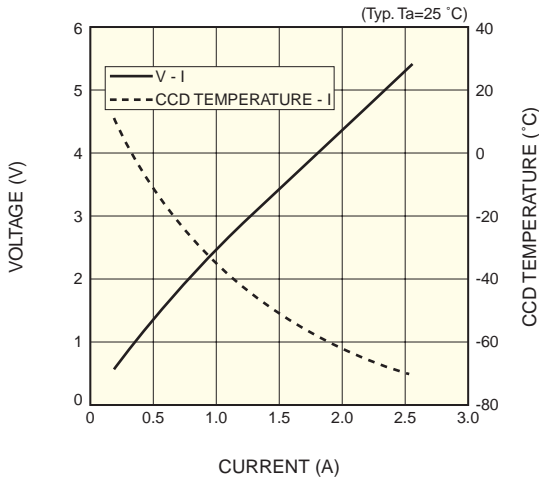
*15: If the current is greater than I_{max}, the heat absorption begins to decrease due to the Joule heat. It should be noted that this value is not a damage threshold. To protect the thermoelectric cooler (Peltier element) and maintain stable operation, the supply current should be less than 60 % of this maximum current.

*16: Temperature at hot side of thermoelectric cooler.

*17: ΔT=Th - Tc

*18: This is a theoretical heat absorption level that offsets the temperature difference in the TE-cooled element when the maximum current is supplied to the unit.

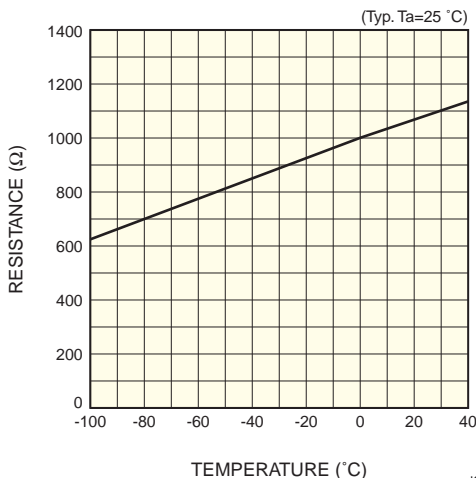
*19: Temperature at cool side of thermoelectric cooler.



KMPDB0107EA

■ Specifications of built-in temperature sensors (S9736-02)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Resistance at cool side	R _c	T=0 °C	-	1000	-	Ω
Temperature coefficient of resistance at cool side	-	-	-	0.00375	-	Ω/Ω
Resistance at hot side	R _h	T=0 °C	-	1000	-	Ω
Temperature coefficient of resistance at hot side	-	-	-	0.00385	-	Ω/Ω



KMPDB0108EA

■ Precaution for use (electrostatic countermeasures)

- Handle these sensors with bare hands or wearing cotton gloves. In addition, wear anti-static clothing or use a wrist strap, in order to prevent electrostatic damage due to electrical charges from friction.
- Avoid directly placing these sensors on a work-desk or work-bench that may carry an electrostatic charge.
- Provide ground lines or ground connection with the work-floor, work-desk and work-bench to allow static electricity to discharge.
- Ground the tools used to handle these sensors, such as tweezers and soldering irons.

It is not always necessary to provide all the electrostatic measures stated above. Implement these measures according to the amount of damage that occurs.

■ Element cooling/heating temperature incline rate

Element cooling/heating temperature incline rate should be set at less than 5 K/min.

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HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184, <http://www.hamamatsu.com>

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741